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# $0.5\ \Omega$ CMOS, 1.8 V to 5.5 V, Dual SPDT/2:1 Mux, Mini LFCSP

### **ADG854**

#### **FEATURES**

0.8  $\Omega$  typical on resistance Less than 1  $\Omega$  maximum on resistance at 85°C 1.8 V to 5.5 V single supply High current carrying capability: 300 mA continuous Rail-to-rail switching operation Fast-switching times: <17 ns Typical power consumption: <0.1  $\mu$ W 1.30 mm × 1.60 mm mini LFCSP

#### **APPLICATIONS**

Cellular phones PDAs MP3 players Power routing Battery-powered systems PCMCIA cards Modems Audio and video signal routing Communication systems

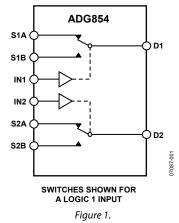
#### **GENERAL DESCRIPTION**

The ADG854 is a low voltage CMOS device containing two independently selectable single-pole, double-throw (SPDT) switches. This device offers ultralow on resistance of <1  $\Omega$  over the full temperature range. The ADG854 is fully specified for 5.5 V and 3.3 V supply operation.

Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. The ADG854 exhibits break-before-make switching action.

The ADG854 is available in a 1.3 mm  $\times$  1.6 mm 10-lead mini LFCSP.

#### FUNCTIONAL BLOCK DIAGRAM



#### **PRODUCT HIGHLIGHTS**

- 1. <1  $\Omega$  over full temperature range of -40°C to +85°C.
- 2. Single 1.8 V to 5.5 V operation.
- 3. Compatible with 1.8 V CMOS logic.
- 4. High current handling capability: 300 mA continuous current per channel.
- 5. Low THD + N: 0.08% typical.
- 6. 1.30 mm × 1.60 mm mini LFCSP.

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# ADG854\* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

### COMPARABLE PARTS

View a parametric search of comparable parts.

### EVALUATION KITS

• ADG854 Evaluation Board

### **DOCUMENTATION**

#### Data Sheet

- ADG854: 0.5  $\Omega$  CMOS, 1.8 V to 5.5 V, Dual SPDT/2:1 Mux, Mini LFCSP

#### **User Guides**

• UG-401: Evaluating the ADG854, 0.5 Ω CMOS, 1.8 V to 5.5 V, Dual SPDT/2:1 Mux in Mini LFCSP Package

### REFERENCE MATERIALS

#### **Product Selection Guide**

• Switches and Multiplexers Product Selection Guide

### DESIGN RESOURCES

- ADG854 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

### DISCUSSIONS

View all ADG854 EngineerZone Discussions.

### SAMPLE AND BUY

Visit the product page to see pricing options.

### **TECHNICAL SUPPORT**

Submit a technical question or find your regional support number.

### DOCUMENT FEEDBACK

Submit feedback for this data sheet.

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#### **REVISION HISTORY**

6/08—Revision 0: Initial Version

### **SPECIFICATIONS**

 $V_{\text{DD}}$  = 4.2 V to 5.5V, GND = 0 V, unless otherwise noted.

#### Table 1.

Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH	1			
Analog Signal Range		0 to V <sub>DD</sub>	V	
On Resistance, R <sub>ON</sub>	0.8		Ωtyp	$V_{DD} = 4.2 V$ , $V_{S} = 0 V$ to $V_{DD}$ , $I_{DS} = 100 m$ A; see Figure 16
	0.85	1	Ωmax	
On Resistance Match Between Channels, $\Delta R_{ON}$	0.02		Ωtyp	$V_{DD} = 4.2 \text{ V}, V_{S} = 0 \text{ V} \text{ to } V_{DD}, I_{DS} = 100 \text{ mA}$
		0.04	Ωmax	
On Resistance Flatness, R <sub>FLAT (ON)</sub>	0.17		Ωtyp	$V_{DD} = 4.2 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{ V}_{DD}, \text{ I}_{\text{DS}} = 100 \text{ mA}$
		0.23	Ωmax	
LEAKAGE CURRENTS				$V_{DD} = 5.5 V$
Source Off Leakage, Is (Off)	±10		pA typ	$V_{s} = 0.6 V/4.2 V, V_{D} = 4.2 V/0.6 V$ ; see Figure 17
Channel On Leakage, I <sub>D</sub> , I <sub>s</sub> (On)	±30		pA typ	$V_{s} = V_{D} = 0.6 V$ or 4.2 V; see Figure 18
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.0	V min	
Input Low Voltage, VINL		0.8	V max	
Input Current				
Iinl or Iinh	0.002		μA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
		0.05	µA max	
Digital Input Capacitance, C <sub>IN</sub>	2.5		pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>			. ,.	
t <sub>on</sub>	17		ns typ	$R_{L} = 50 \Omega, C_{L} = 35 pF$
	23	28	ns max	$V_s = 3 V/0 V$ ; see Figure 19
t <sub>off</sub>	6		ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	8.5	9.2	ns max	$V_s = 3 V$ ; see Figure 19
Break-Before-Make Time Delay, t <sub>BBM</sub>	14		ns typ	$R_L = 50 \Omega$ , $C_L = 35 pF$
		8	ns min	$V_{s1} = V_{s2} = 1.5 V$ ; see Figure 20
Charge Injection	30		pC typ	$V_s = 1.5 V$ , $R_s = 0 \Omega$ , $C_L = 1 nF$ ; see Figure 21
Off Isolation	-75		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 100 kHz; see Figure 22
Channel-to-Channel Crosstalk	-85		dB typ	S1A to S2A/S1B to S2B, $R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 \text{ kHz}$ ; see Figure 25
	-73		dB typ	S1A to S1B/S2A to S2B, $R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 100 kHz; see Figure 24
Total Harmonic Distortion + Noise, THD + N	0.08		% typ	$R_L = 32 \Omega$ , f = 20 Hz to 20 kHz, V <sub>s</sub> = 3.5 V p-p
Insertion Loss	-0.06		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 23
–3 dB Bandwidth	100		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 23
Cs (Off)	19.5		pF typ	$\begin{bmatrix} 1 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix} = \begin{bmatrix} 1 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$
$C_{\rm D}, C_{\rm S}$ (On)	50		pF typ	
POWER REQUIREMENTS	50		hi ûh	V <sub>DD</sub> = 5.5 V
	0.002		uA tun	$V_{DD} = 5.5 V$ Digital inputs = 0 V or 5.5 V
l <sub>DD</sub>	0.002	1.0	μΑ typ μΑ max	
		1.0	µн тах	

<sup>1</sup> Guaranteed by design, not subject to production test.

 $V_{\rm DD}$  = 2.7 V to 3.6 V, GND = 0 V, unless otherwise noted.

#### Table 2.

Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 to V <sub>DD</sub>	V	
On Resistance, R <sub>ON</sub>	1.3		Ωtyp	$V_{DD} = 2.7 V$ , $V_s = 0 V$ to $V_{DD}$ , $I_{Ds} = 100 m$ A; see Figure 16
	1.5	1.7	Ωmax	
On Resistance Match Between Channels, $\Delta R_{ON}$	0.03		Ωtyp	$V_{DD} = 2.7 \text{ V}, V_{S} = 0.6 \text{ V}, I_{DS} = 100 \text{ mA}$
		0.05	Ωmax	
On Resistance Flatness, R <sub>FLAT (ON)</sub>	0.48		Ωtyp	$V_{DD} = 2.7 \text{ V}, V_{S} = 0 \text{ V} \text{ to } V_{DD}, I_{DS} = 100 \text{ mA}$
		0.66	Ωmax	
LEAKAGE CURRENTS				$V_{DD} = 3.6 V$
Source Off Leakage, I <sub>s</sub> (Off)	±10		pA typ	$V_s = 0.6 V/3.3 V$ , $V_D = 3.3 V/0.6 V$ ; see Figure 17
Channel On Leakage, I <sub>D</sub> , I <sub>s</sub> (On)	±30		pA typ	$V_{s} = V_{D} = 0.6 V$ or 3.3 V; see Figure 18
DIGITAL INPUTS			. ,.	
Input High Voltage, V <sub>INH</sub>		1.35	V min	
Input Low Voltage, V <sub>INL</sub>		0.7	V max	
Input Current				
I <sub>INL</sub> or I <sub>INH</sub>	0.002		µA typ	$V_{IN} = V_{GND} \text{ or } V_{DD}$
		0.05	µA max	
Digital Input Capacitance, C <sub>IN</sub>	4		pF typ	
DYNAMIC CHARACTERISTICS <sup>1</sup>				
ton	25		ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	37	43	ns max	$V_s = 1.5 V/0 V$ ; see Figure 19
toff	7		ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	7.4	8	ns max	$V_s = 1.5 V$ ; see Figure 19
Break-Before-Make Time Delay, tBBM	22		ns typ	$R_L = 50 \Omega$ , $C_L = 35 pF$
		13	ns min	$V_{s1} = V_{s2} = 1$ V; see Figure 20
Charge Injection	23		pC typ	$V_s = 1.5 V$ , $R_s = 0 V$ , $C_L = 1 nF$ ; see Figure 21
Off Isolation	-75		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 100 kHz$ ; see Figure 22
Channel-to-Channel Crosstalk	-85		dB typ	S1A to S2A/S1B to S2B; $R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 100 kHz; see Figure 25
	-73		dB typ	S1A to S1B/S2A to S2B; $R_L = 50 \Omega$ , $C_L = 5 pF$ , f = 100 kHz; see Figure 24
Total Harmonic Distortion, THD	0.15		% typ	$R_L = 32 \Omega$ , f = 20 Hz to 20 kHz, V <sub>s</sub> = 1.5 V p-p
Insertion Loss	-0.07		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 23
–3 dB Bandwidth	100		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 23
Cs (Off)	20		pF typ	
C <sub>D</sub> , C <sub>s</sub> (On)	52		pF typ	
POWER REQUIREMENTS				V <sub>DD</sub> = 3.6 V
l <sub>DD</sub>	0.002		μA typ	Digital inputs = $0 \text{ V}$ or $3.6 \text{ V}$
		1.0	µA max	

<sup>1</sup> Guaranteed by design, not subject to production test.

### ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$ , unless otherwise noted.

#### Table 3.

Parameter	Rating
V <sub>DD</sub> to GND	–0.3 V to +6 V
Analog Inputs <sup>1</sup>	-0.3 V to V <sub>DD</sub> + 0.3 V
Digital Inputs <sup>1</sup>	–0.3 V to V <sub>DD</sub> + 0.3 V or 10 mA, whichever occurs first
Peak Current per Channel, S or D	500 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current per Channel, S or D	300 mA
Operating Temperature Range	–40°C to +85°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
10-Lead Mini LFCSP	
θ <sub>JA</sub> Thermal Impedance, 3-Layer Board	131.6°C/W
Reflow Soldering, Pb-Free	
Peak Temperature	260(+0/-5)°C
Time at Peak Temperature	10 sec to 40 sec

<sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

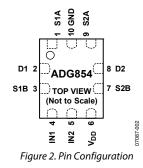
Only one absolute maximum rating may be applied at any one time.

#### **ESD CAUTION**



**ESD** (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

### **PIN CONFIGURATION AND FUNCTION DESCRIPTION**



#### **Table 4. Pin Function Descriptions**

Pin No.	Mnemonic	Description	
1, 3, 7, 9	S1A, S1B, S2B, S2A	Source Terminal. This pin can be an input or output.	
2, 8	D1, D2	Drain Terminal. This pin can be an input or output.	
4	IN1	Logic Control Input.	
5	IN2	Logic Control Input.	
6	V <sub>DD</sub>	Most Positive Power Supply Potential.	
10	GND	Ground (0 V) Reference.	

#### Table 5. ADG854 Truth Table

Logic (IN1/IN2)	Switch A (S1A or S2A)	Switch B (S1B or S2B)
0	Off	On
1	On	Off

### **TYPICAL PERFORMANCE CHARACTERISTICS**

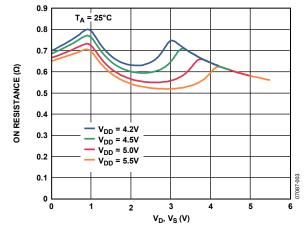


Figure 3. On Resistance vs.  $V_D$  ( $V_S$ ),  $V_{DD} = 4.2$  V to 5.5 V

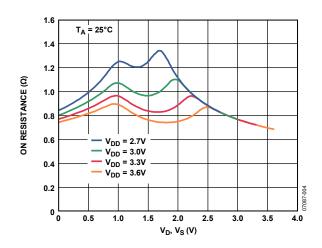


Figure 4. On Resistance vs.  $V_D$  ( $V_S$ ),  $V_{DD} = 2.7$  V to 3.6 V

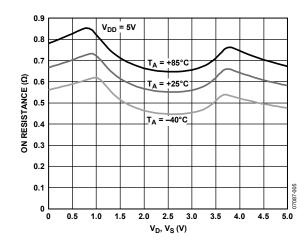


Figure 5. On Resistance vs.  $V_D$  (V<sub>s</sub>) for Different Temperatures,  $V_{DD} = 5 V$ 

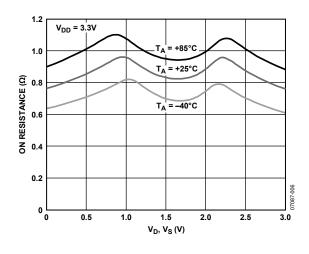


Figure 6. On Resistance vs.  $V_D$  (V<sub>s</sub>) for Different Temperatures,  $V_{DD} = 3.3 V$ 

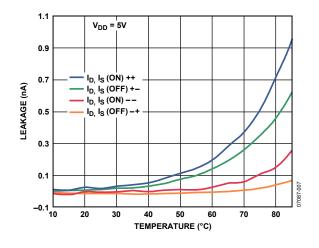


Figure 7. Leakage Current vs. Temperature,  $V_{DD} = 5 V$ 

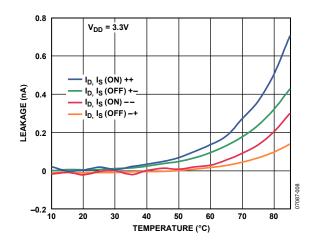
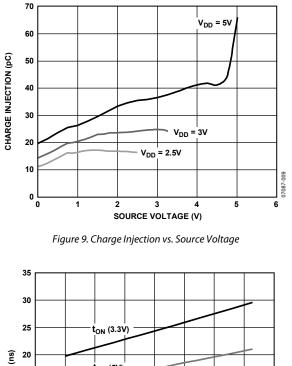


Figure 8. Leakage Current vs. Temperature,  $V_{DD} = 3.3 V$ 



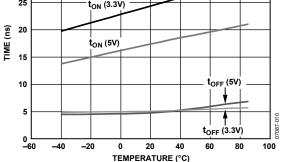
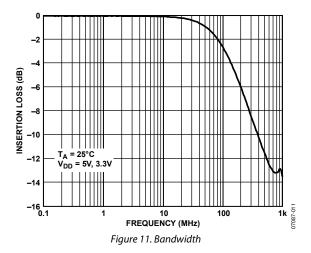
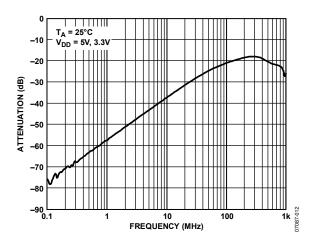
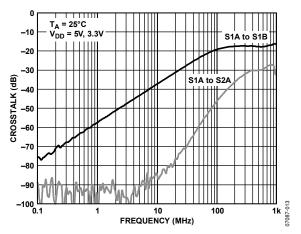


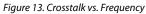
Figure 10. ton/toff Times vs. Temperature











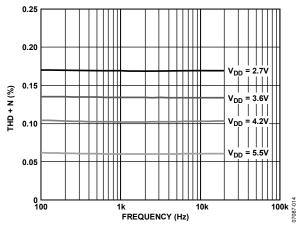
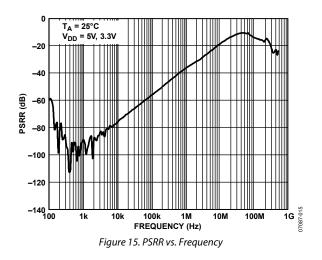
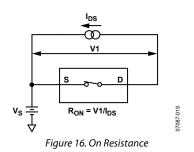
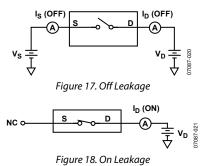


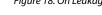
Figure 14. Total Harmonic Distortion + Noise (THD+N) vs. Frequency

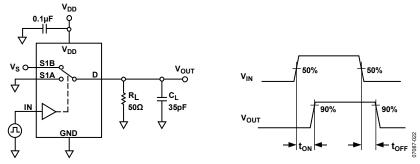


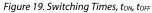
### **TEST CIRCUITS**

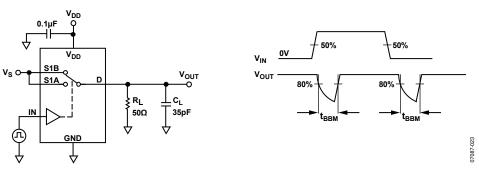














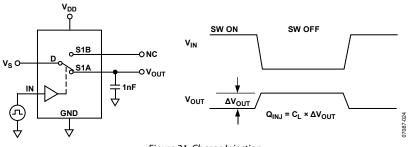
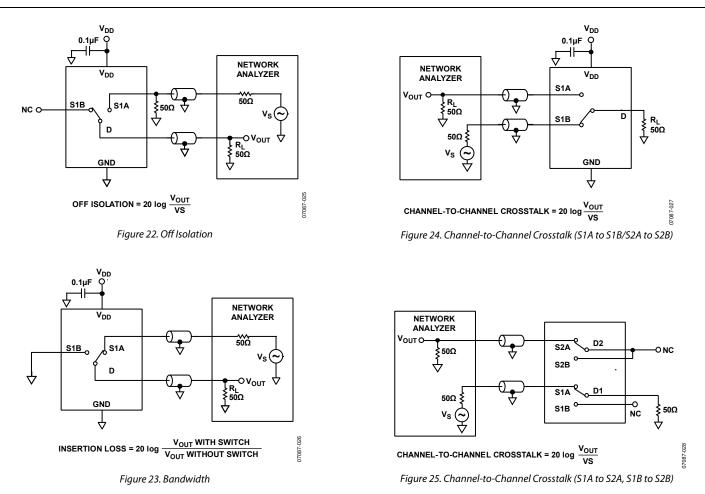


Figure 21. Charge Injection



### TERMINOLOGY

#### Idd

Positive supply current.

#### $V_D (V_s)$

Analog voltage on Terminal D and Terminal S.

Ron

Ohmic resistance between Terminal D and Terminal S.

 $R_{\text{FLAT}\ (ON)}$  The difference between the maximum and minimum values of on resistance as measured on the switch.

 $\Delta R_{\text{ON}}$  On resistance match between any two channels.

Is (Off) Source leakage current with the switch off.

I<sub>D</sub> (Off) Drain leakage current with the switch off.

 $I_{\rm D},\,I_{\rm S}\left(On\right)$  Channel leakage current with the switch on.

V<sub>INL</sub> Maximum input voltage for Logic 0.

V<sub>INH</sub> Minimum input voltage for Logic 1.

 $I_{\text{INL}}\left(I_{\text{INH}}\right)$  Input current of the digital input.

Cs (Off) Off switch source capacitance. Measured with reference to ground.

### C<sub>D</sub> (Off)

Off switch drain capacitance. Measured with reference to ground.

 $C_D, C_S(On)$ 

On switch capacitance. Measured with reference to ground.

Cin

Digital input capacitance.

#### ton

Delay time between the 50% and 90% points of the digital input and switch on condition.

#### toff

Delay time between the 50% and 90% points of the digital input and switch off condition.

**t**<sub>BBM</sub> On or off time measured between the 80% points of both switches when switching from one to another.

#### **Charge Injection**

Measure of the glitch impulse transferred from the digital input to the analog output during on/off switching.

#### **Off Isolation**

Measure of unwanted signal coupling through an off switch.

#### Crosstalk

Measure of unwanted signal that is coupled from one channel to another because of parasitic capacitance.

**–3 dB Bandwidth** Frequency at which the output is attenuated by 3 dB.

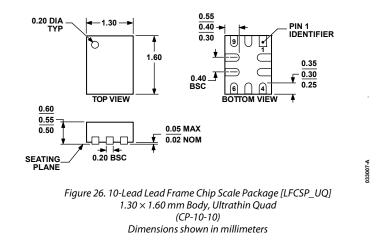
**On Response** Frequency response of the on switch.

**Insertion Loss** The loss due to the on resistance of the switch.

#### THD + N

Ratio of the harmonics amplitude plus noise of a signal to the fundamental.

### **OUTLINE DIMENSIONS**



#### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option	Branding
ADG854BCPZ-REEL <sup>1</sup>	-40°C to +85°C	10-Lead Lead Frame Chip Scale Package [LFCSP_UQ]	CP-10-10	С
ADG854BCPZ-REEL71	-40°C to +85°C	10-Lead Lead Frame Chip Scale Package [LFCSP_UQ]	CP-10-10	С

 $^{1}$  Z = RoHS Compliant Part.

### NOTES

### NOTES

### NOTES

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